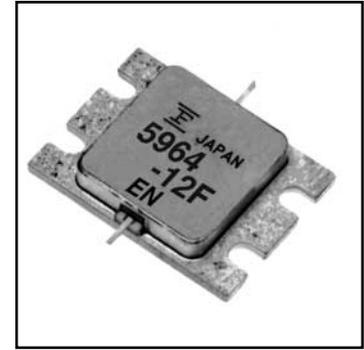


### FEATURES

- High Output Power:  $P_{1dB} = 41.5\text{dBm}$  (Typ.)
- High Gain:  $G_{1dB} = 10.0\text{dB}$  (Typ.)
- High PAE:  $\eta_{add} = 37\%$  (Typ.)
- Low  $IM_3 = -46\text{dBc}$  @  $P_o = 30.5\text{dBm}$
- Broad Band: 5.9 ~ 6.4GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



### DESCRIPTION

The FLM5964-12F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_C = 25^\circ\text{C}$	57.6	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -5.6 mA respectively with gate resistance of 50 $\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	5000	7500	mA
Transconductance	$g_m$	$V_{DS} = 5\text{V}, I_{DS} = 3250\text{mA}$	-	5000	-	mS
Pinch-off Voltage	$V_p$	$V_{DS} = 5\text{V}, I_{DS} = 250\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -250\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10\text{V},$ $I_{DS} = 0.65I_{DSS}$ (Typ.), $f = 5.9 \sim 6.4\text{GHz},$ $Z_S = Z_L = 50\text{ohm}$	40.5	41.5	-	dBm
Power Gain at 1dB G.C.P.	$G_{1dB}$		9.0	10.0	-	dB
Drain Current	$I_{dsr}$		-	3250	3800	mA
Power-added Efficiency	$\eta_{add}$		-	37	-	%
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB
3rd Order Intermodulation Distortion	$IM_3$	$f = 6.4\text{GHz}, \Delta f = 10\text{MHz}$ 2-Tone Test $P_{out} = 30.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	$R_{th}$	Channel to Case	-	2.3	2.6	$^\circ\text{C}/\text{W}$
Channel Temperature Rise	$\Delta T_{ch}$	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

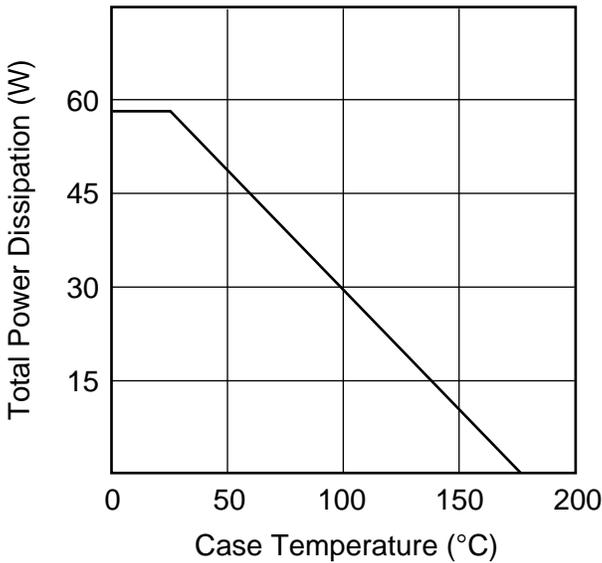
CASE STYLE: IK

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

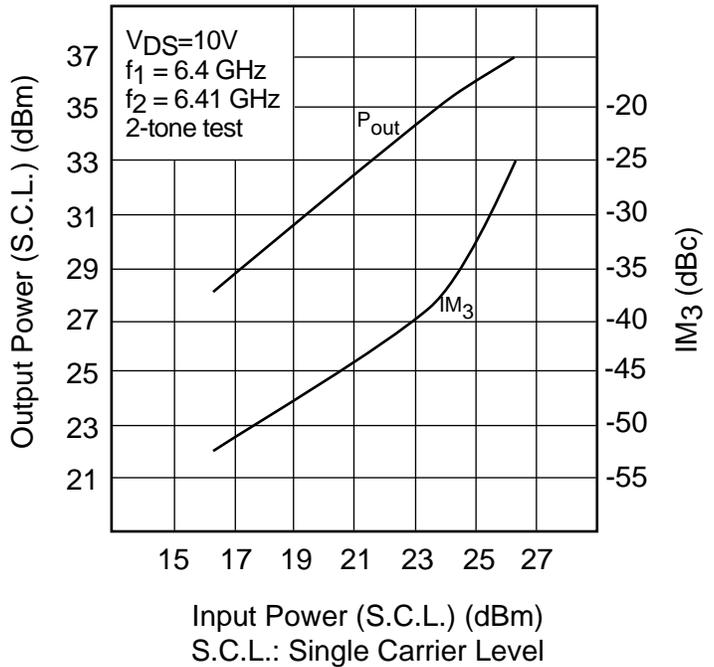
# FLM5964-12F

## C-Band Internally Matched FET

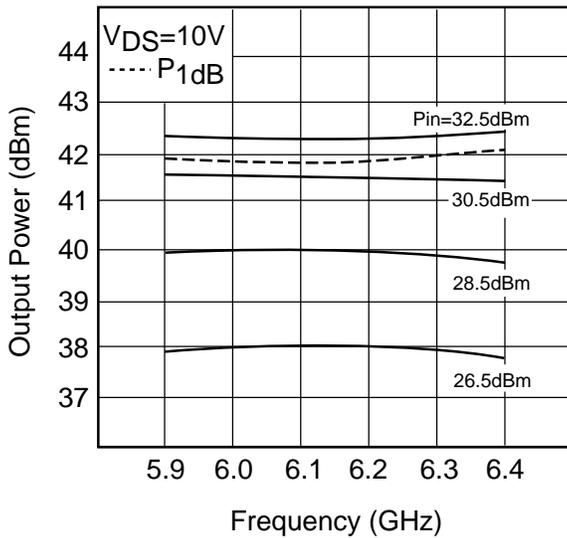
**POWER DERATING CURVE**



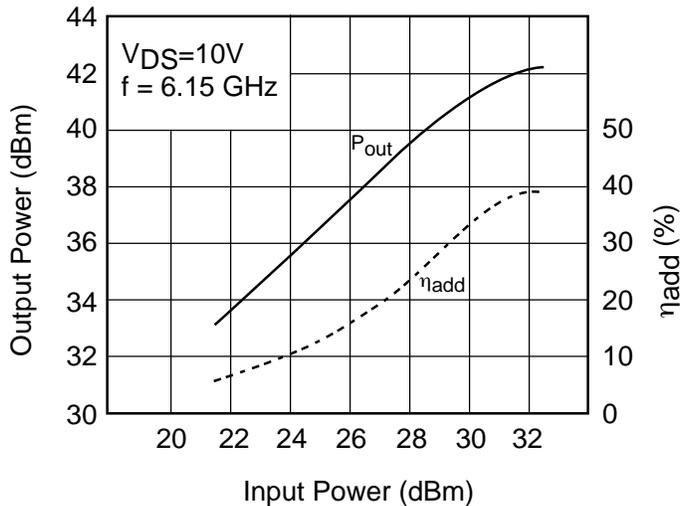
**OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER**



**OUTPUT POWER vs. FREQUENCY**

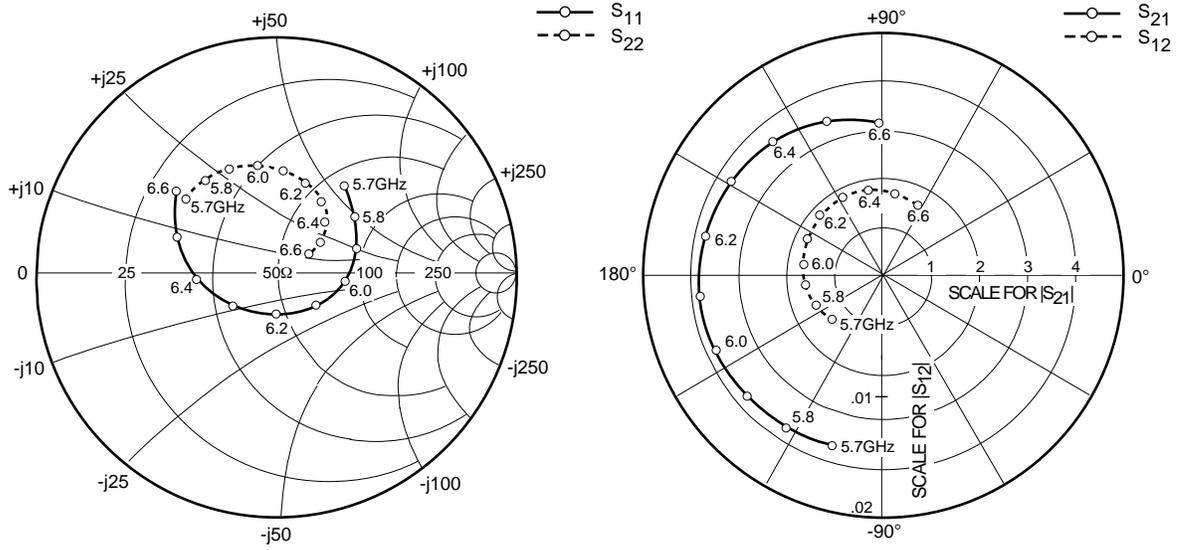


**OUTPUT POWER vs. INPUT POWER**



# FLM5964-12F

## C-Band Internally Matched FET



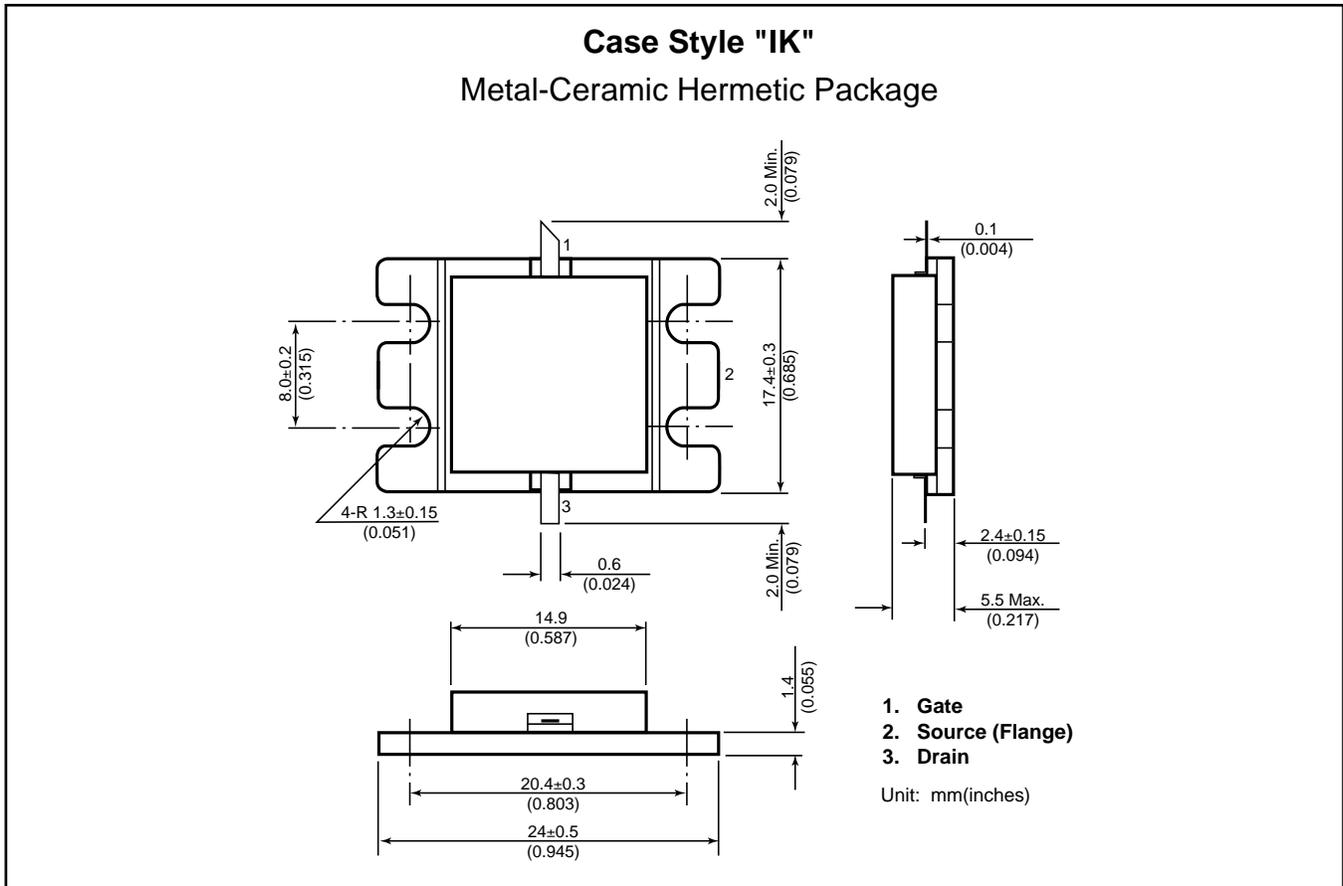
### S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 3250mA$

FREQUENCY (MHZ)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5700	.455	51.2	3.642	-107.3	.056	-140.5	0.496	140.4
5800	.411	34.8	3.713	-123.0	.060	-155.3	0.493	127.1
5900	.354	16.2	3.773	-139.4	.064	-171.6	0.482	113.5
6000	.283	-7.1	3.824	-156.4	.067	171.7	0.465	99.6
6100	.211	-41.1	3.844	-174.2	.070	153.6	0.434	85.9
6200	.181	-92.2	3.822	167.6	.073	136.1	0.401	72.5
6300	.234	-141.8	3.754	148.8	.072	118.7	0.353	59.0
6400	.335	-175.7	3.621	129.6	.072	99.6	0.294	45.6
6500	.442	160.5	3.415	110.5	.069	82.6	0.224	35.2
6600	.536	140.5	3.173	91.5	.065	64.5	0.153	30.8

# FLM5964-12F

## C-Band Internally Matched FET



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### CAUTION

Fujitsu Compound Semiconductor Products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.